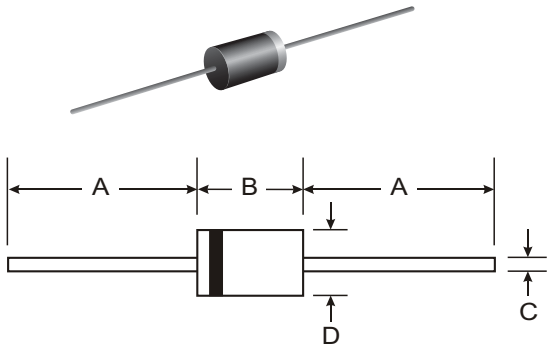
10JDA10

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 100V
CURRENT: 1.0 A

Features

- Miniature Size
- Low Forward Voltage drop
- Low Reverse Leakage Current
- High Surge Capability



DO-41		
Dim	**Min**	**Max**
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Mechanical Data

- Case: D O - 4 1 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

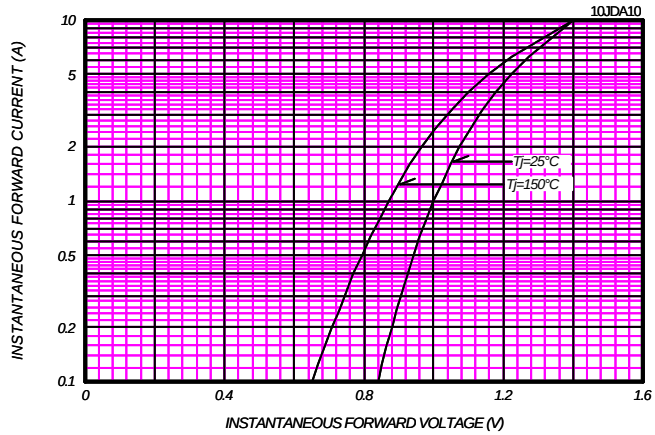
Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	10JDA10			Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100			V
Average Rectified Output Current	I_O	50Hz Half Sine Wave Resistive Load	Ta=29℃ *1	1.0	A
			Tl=126℃ (Tl: Lead Temperature)	1.0	
RMS Forward Current	$I_{F(RMS)}$			1.57	A
Surge Forward Current	I_{FSM}	50Hz Half Sine Wave,1cycle, Non-repetitive		45	A
Operating JunctionTemperature Range	T_{jw}	- 40 to + 150			℃
Storage Temperature Range	T_{stg}	- 40 to + 150			℃

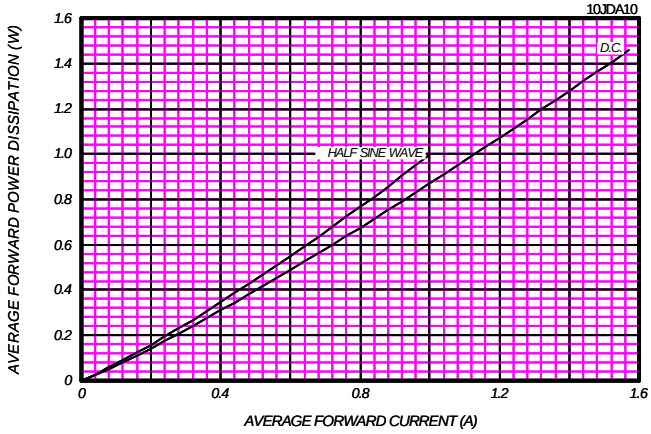
Electrical Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	Tj= 25℃, V_{RM}= V_{RRM}	-	-	10	μA
Peak Forward Voltage	V_{FM}	Tj= 25℃, I_{FM}= 1.0A	-	-	1.0	V
Thermal Resistance	Rth(j-a)	Junction to Ambient *1	-	-	120	℃/W
	Rth(j-l)	Junction to Lead	-	-	23	

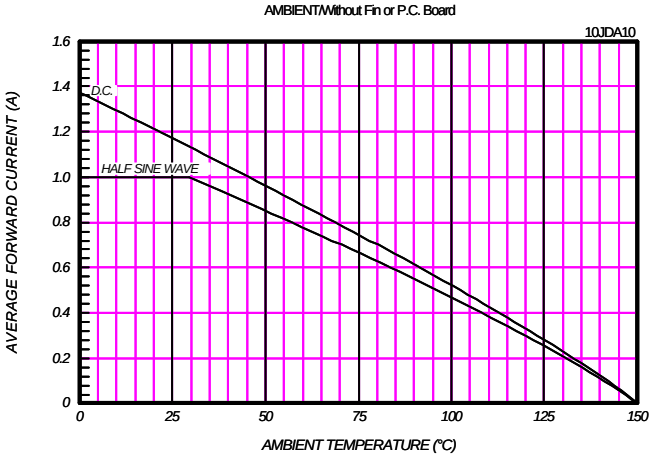
FORWARD CURRENT VS. VOLTAGE



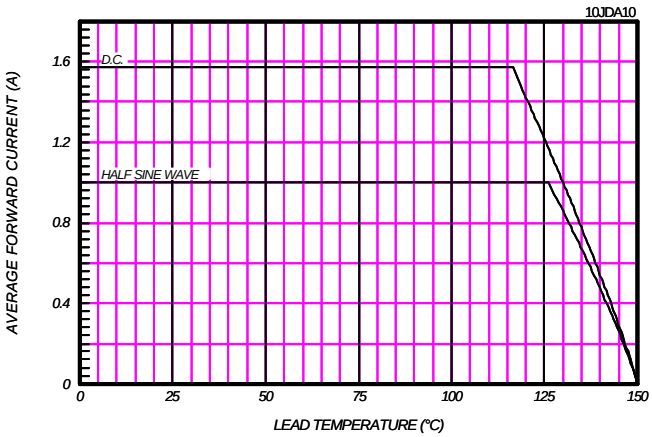
AVERAGE FORWARD POWER DISSIPATION



AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE



AVERAGE FORWARD CURRENT VS. LEAD TEMPERATURE



SURGE CURRENT RATINGS